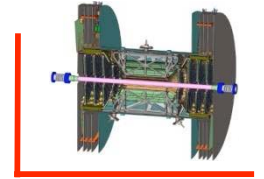


Sensors/FPHX Readout Chip

WBS 1.4.1/1.4.2

Jon S Kapustinsky

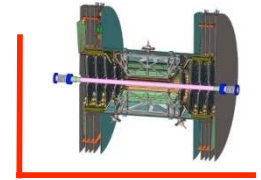
Design Decisions Leading to the FVTX Sensor Wedge and FPHX



Technical risk minimization the key driver

- Mini-strips maintain good resolution in r and ϕ with reasonable occupancy and manageable channel count
- Wire bonds replace initial idea to use bump bonds
- Chip placement moved from centerline of sensor to the edges
 - minimizes potential noise coupling between chip and sensor
 - facilitates implementation of decoupling between sensor bias and chip reference and avoids long path-length sensor return to ground
- Wedge assembly unit based on ease of assembly
- HDI designed to match standard industry capability
- Readout architecture of the FPHX draws on previous successful designs; FPIX2, FSSR, and the SVX family of readout chips
- Low power design of the FPHX simplifies cooling and mechanics significantly

FVTX Section View



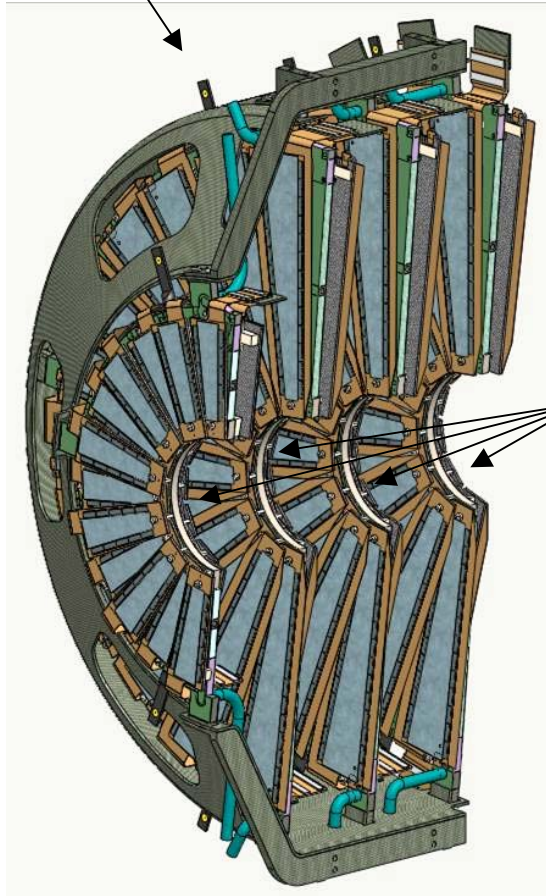
- Four disks on each side

- One small disk (~50mm) three large disks (~126mm)

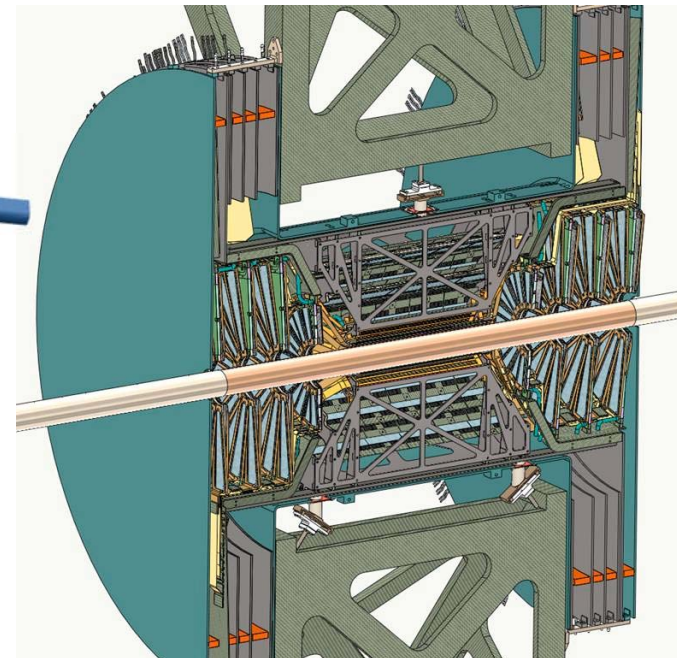
- Mini-strips of 75 micron radial pitch: 3.45 -11.2 mm (large) and 3.45 – 6.55 mm (small)

1/2 of the Barrel

1/2 of one endcap



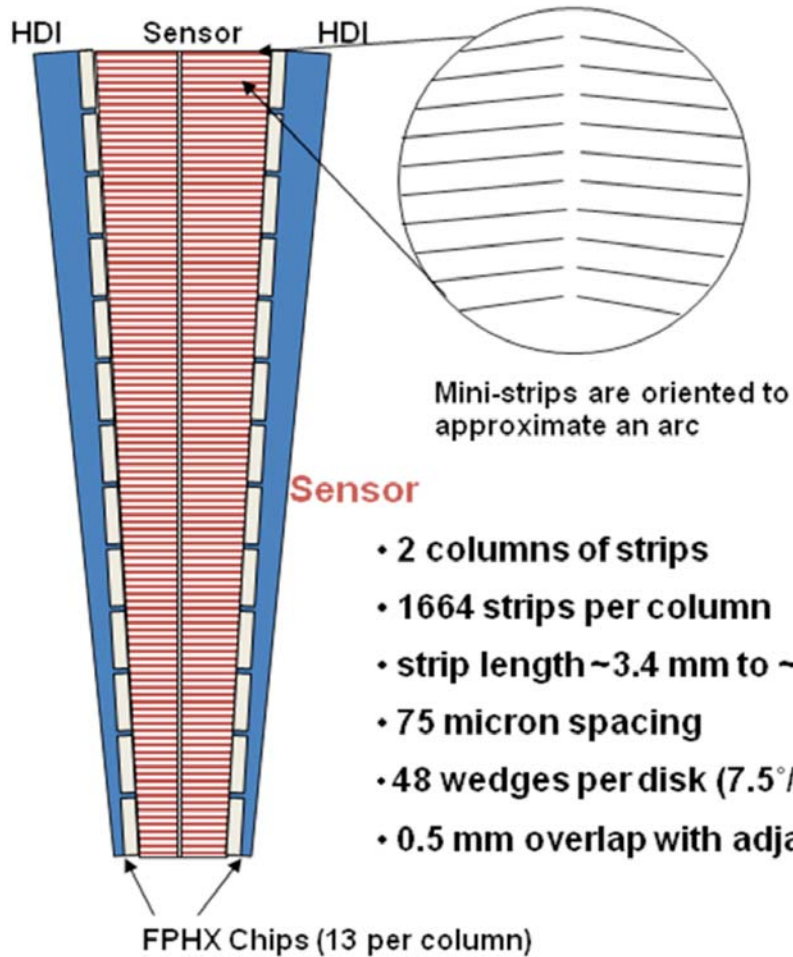
1/2 disks



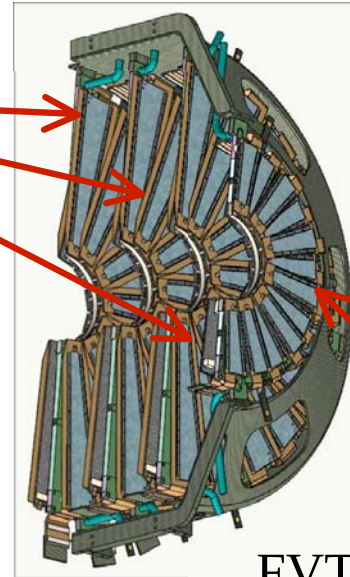
- Total strip count: 2 * 540,672 strips (zero suppressed)

- Total chip count: 2 * 4224 chips

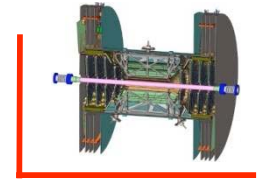
FVTX Sensor Long Wedge



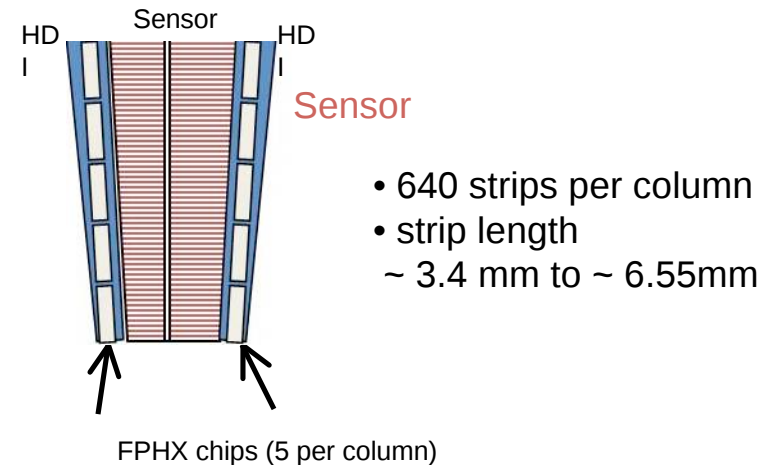
Overall length 126.8 mm
Overall width 8.8 mm i.r., 25.4 mm o.r.



4 hermetic disks, $z = 18.5$ to 38 cm

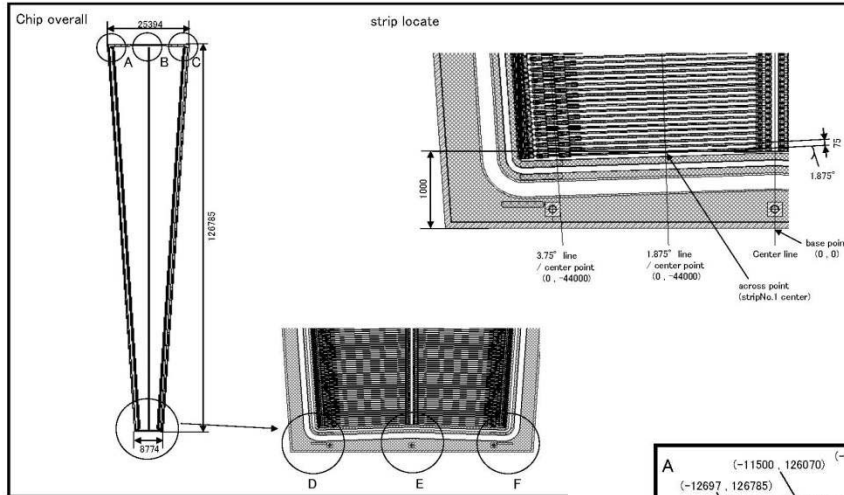
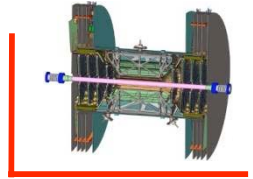


FVTX Sensor Short Wedge



Overall length 50.1 mm
Overall width 8.8 mm i.r., 15.3 o.r.

FVTX Sensors



UNM Probe station
photo



p-implant on n-bulk
ac-coupled
1.5 M Ω polysilicon
resistors
Depletion voltage < 100V
Resistivity 3 to 5 k Ω -cm
Double Pad Rows

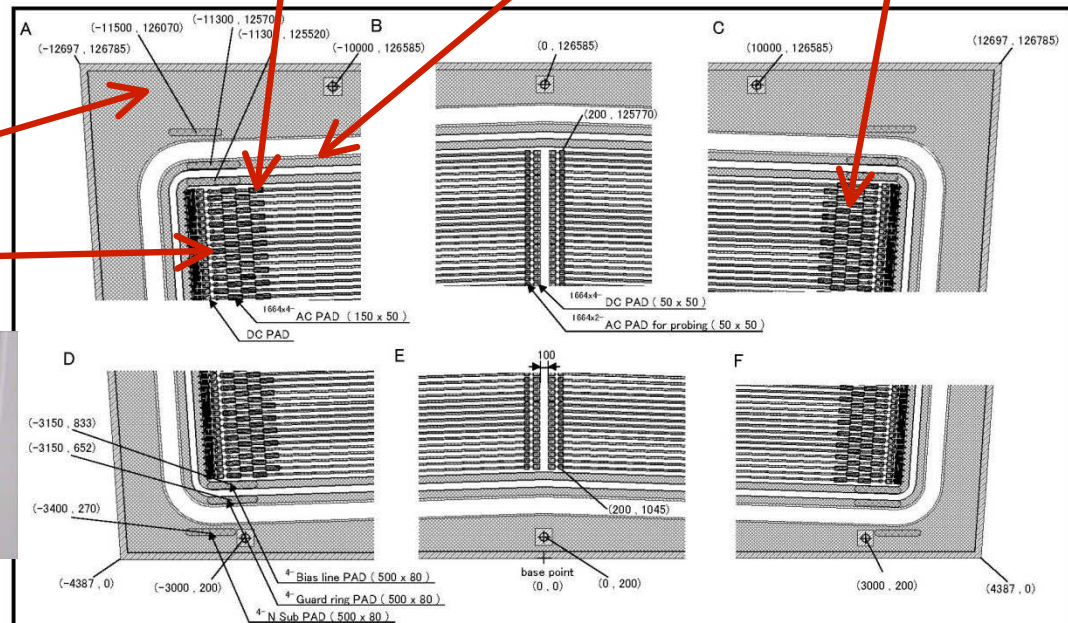
P-Bias Ring

P-Guard Ring

N-Surround

Polysilicon Resistors

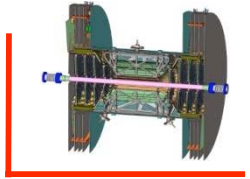
UNM Probe station photo



Initial Prototype, ON-Semi

Current Prototype, Hamamatsu – shipped 31 October, 2008

QA Silicon Sensor Wedges



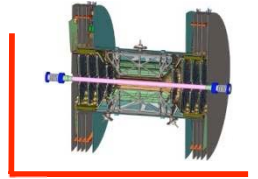
Complete QA specifications on file

- Visual inspection to identify processing or handling flaws
- Current versus voltage characteristic curve for each sensor
- Capacitance versus voltage characteristic curve for each sensor
- Full depletion voltage and breakdown voltage for each sensor

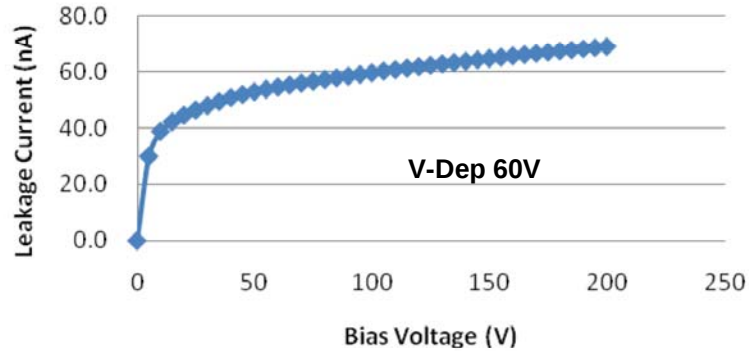
Sensors delivered from Hamamatsu are fully tested

- Coupling capacitor integrity or short for each strip
- Implant open or short for each strip
- Polysilicon resistor open or short for each resistor

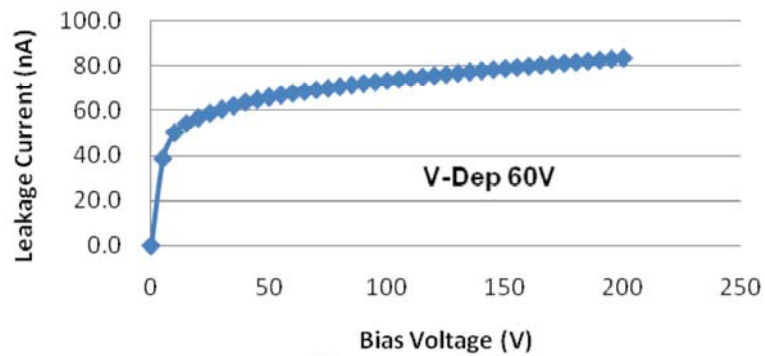
I/V Curves for Prototypes



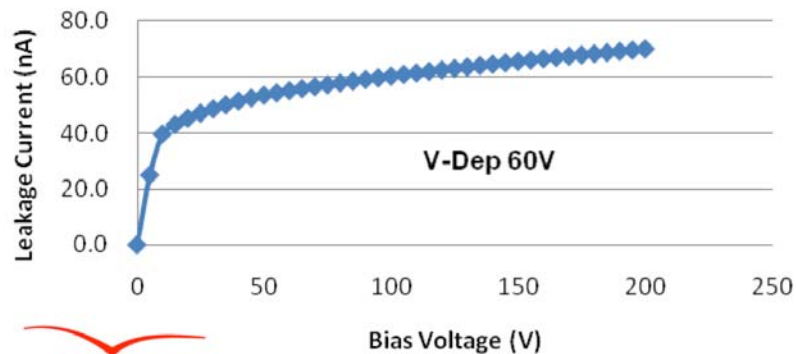
Sensor 1



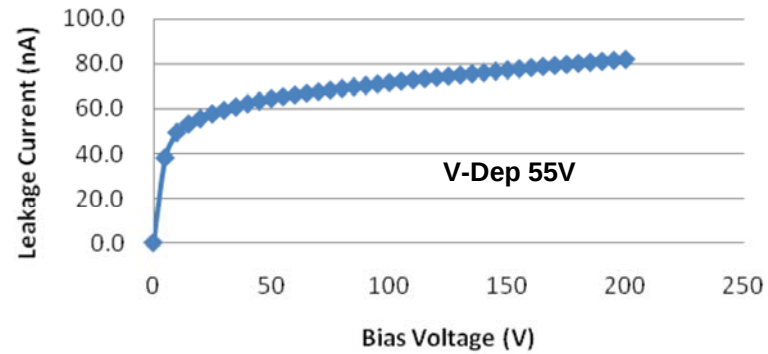
Sensor 2



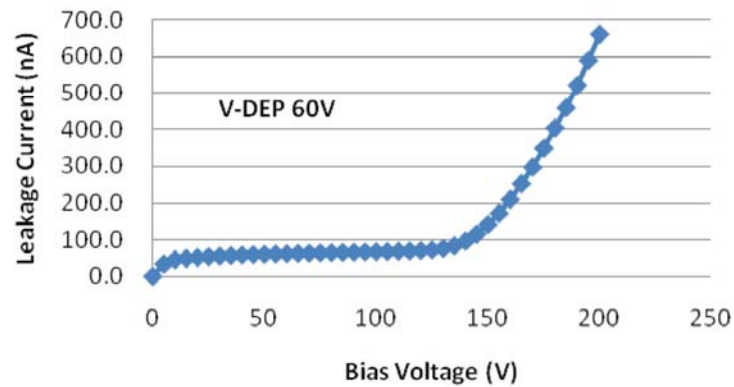
Sensor 3



Sensor 4

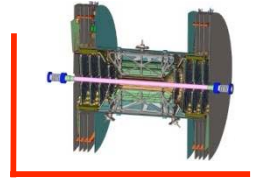


Sensor 5



All strips on all 5 sensors are 100% good!

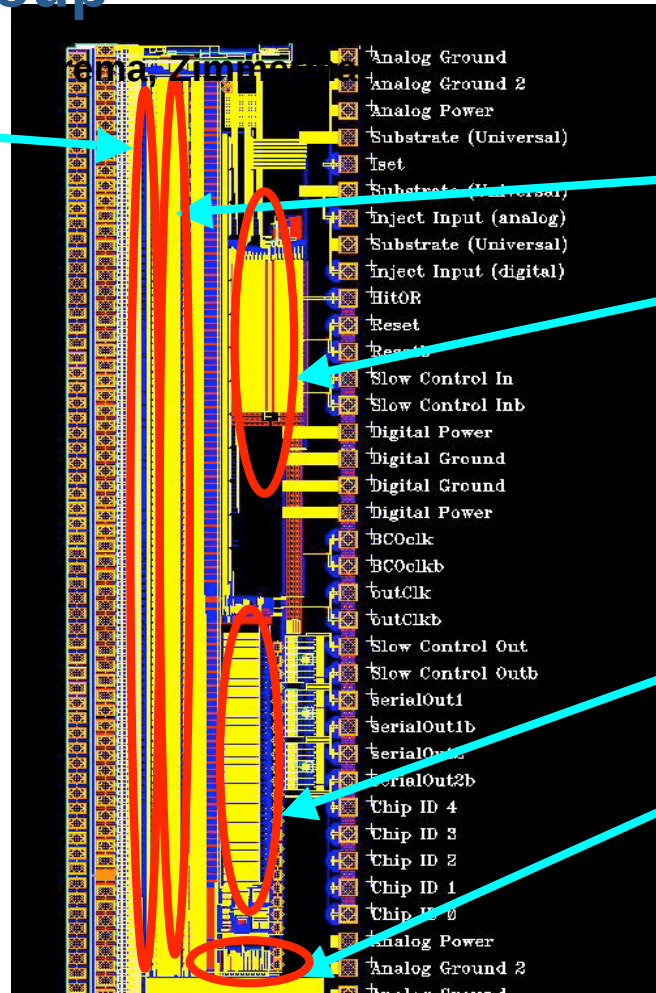
QA sensor manpower and facilities



- 20 silicon sensors in a prototype run
- > 3 months in the schedule to QA prototypes
- Initial tests overseen by experts (Kapustinsky, Fields)
- 330 large, and 110 small silicon sensor wedges required for full FVTX, including spares (fully tested by Hamamatsu)
- Technician and student manpower QA over 5 months
- Test facilities exist at UNM, Prague

FPHX readout chip FNAL ASIC Group

Hoff,
Front End



Chip size 2.7 x 9.1 mm

Core

Slow Controller

FIFO/
Serialize

Phase
Block

Program gain and Vref

Input

Integrator

Vref

Shaper

Disc
outputs

3-bit ADC

Vth0

Comp

Vth1

Comp

Comp

Vth7

Programmable
Thresholds

128 channel

50, 66, 100, 200 mV/fC

60 ns peak time (rt-pgmb1)

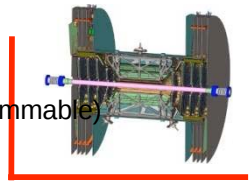
3-bit ADC (th-pgmb1)

Optimized to 1 to 2.5 pf input

115e + 134e/pf

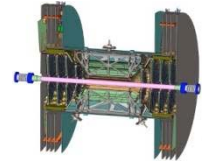
~ 70 to 140 uW/ch (dep. gain)

T-peak ~ 60 ns (programmable)



Fully functional chip design submitted through MOSIS
TSMC 0.25 micron process (delivered Aug. 08)

FPHX Test Stand at LANL

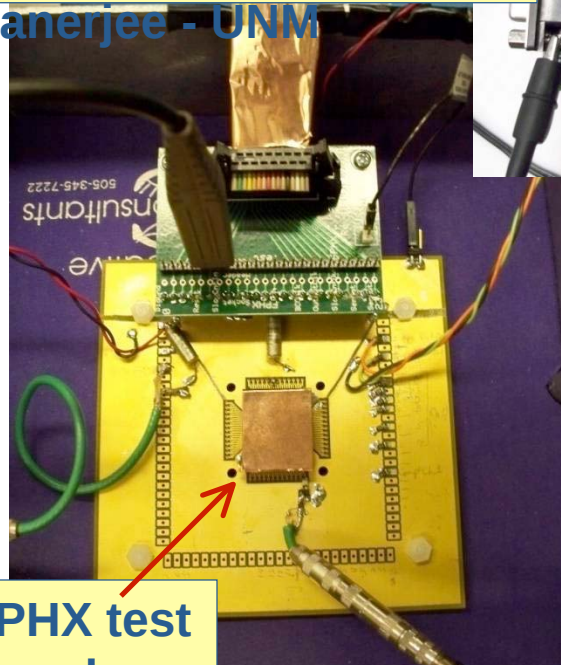
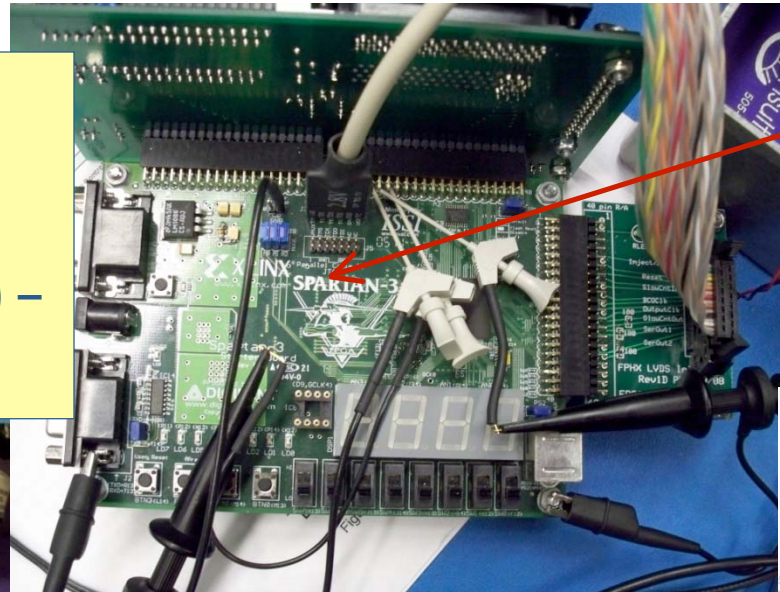


FPHX Test Stand

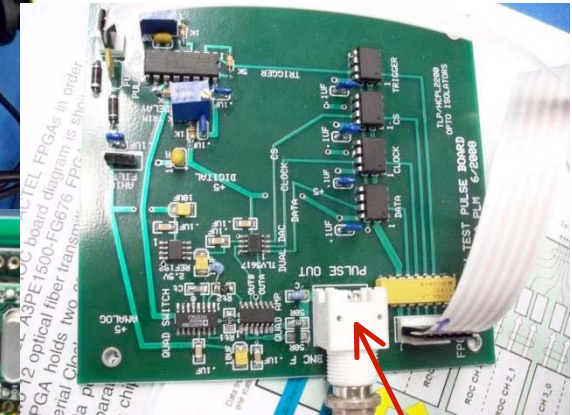
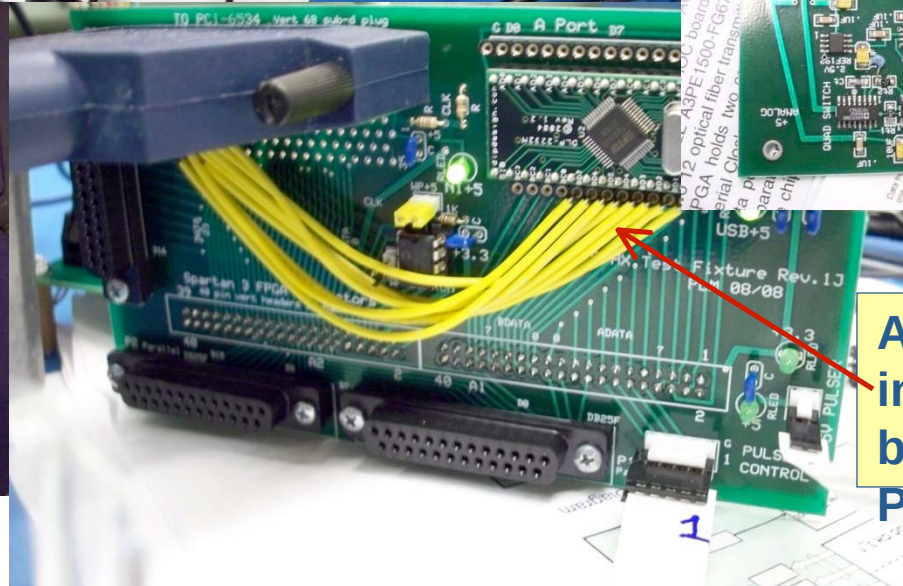
Brooks, Butsyk (PD),
Kapustinsky,
McGaughey, You (PD) –
LANL

Banerjee - UNM

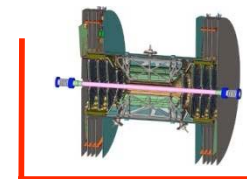
FPGA logic design
and programming –
Sergey Butsyk (LANL
PD)



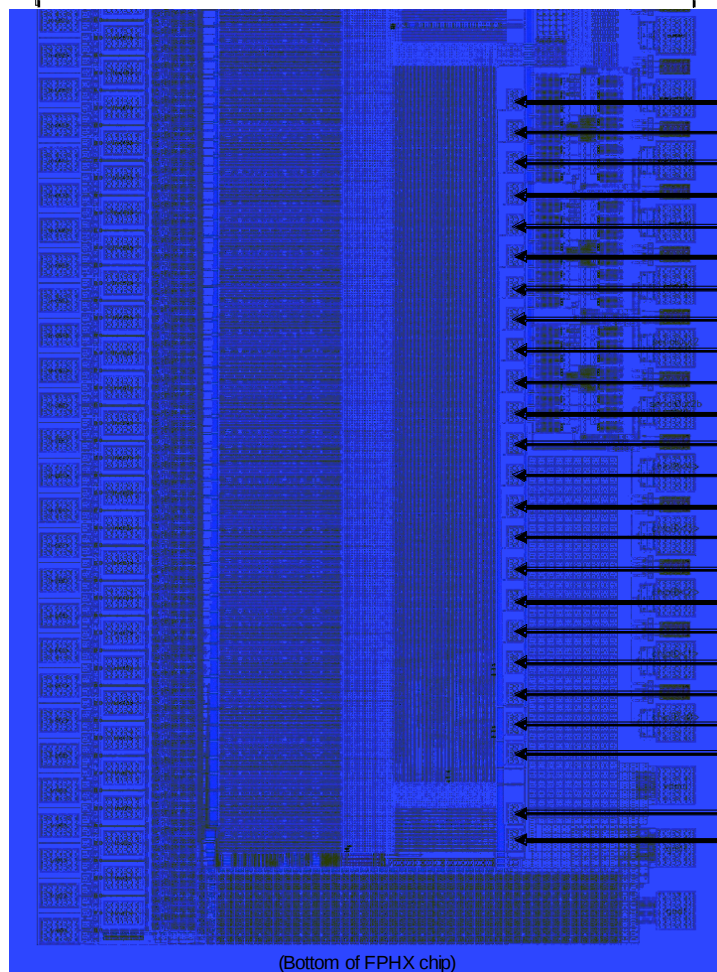
FPHX test
board



Analog pulse
inject, interface
boards
Pat McGaughey



Bondable Test Pads (prototype chip only)



(Bottom of FPHX chip)

- Ch. 14 Comparator0 buffered output, bias with 51K to ground
- Ch. 13 Comparator0 ...
- Ch. 12 Comparator0 ...
- Ch. 11 Comparator0 ...
- Ch. 10 Comparator0 ...
- Ch. 9 Comparator0 ...
- Ch. 8 Comparator0 ...
- Ch. 7 Comparator0 ...
- Ch. 6 Comparator0 ...
- Ch. 5 Comparator0 ...
- Ch. 4 Comparator0 ...
- Ch. 3 Comparator0 ...
- Ch. 2 Comparator0 ...
- Ch. 1 Comparator0 ...
- Ch. 0 Comparator7 ...
- Ch. 0 Comparator6 ...
- Ch. 0 Comparator5 ...
- Ch. 0 Comparator4 ...
- Ch. 0 Comparator3 ...
- Ch. 0 Comparator2 ...
- Ch. 0 Comparator1 ...
- Ch. 0 Comparator0 buffered output, bias with 51K to ground
- Ch. 0 Shaper buffered output, bias with 51K to -10V
- Ch. 0 Integrator buffered output, bias with 39K to +20V

Anticipated changes in production round

- Drop spy pads
- Select optimum W/L for input transistor
- Enable R/O on either serial line
- Add 7th time stamp bit

Figure 26.

FPHX Preliminary Tests

Simulation results

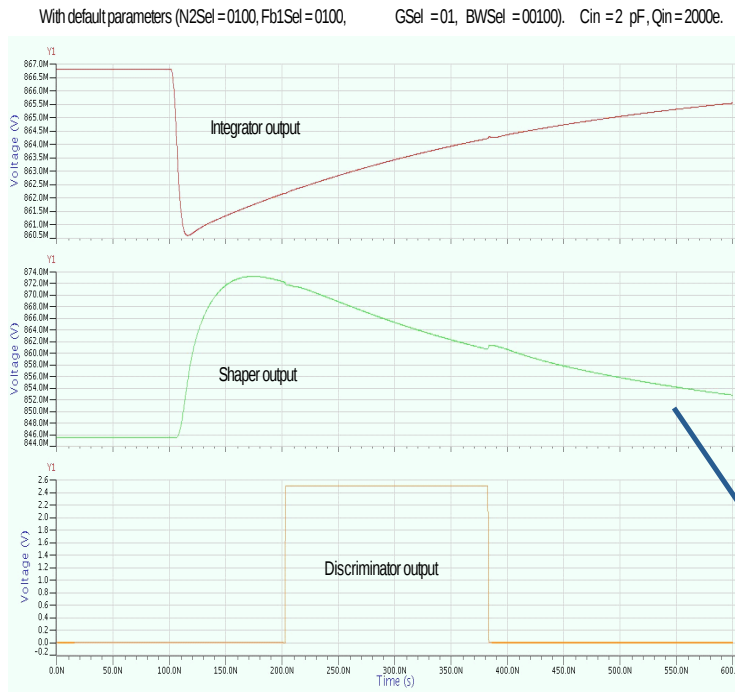
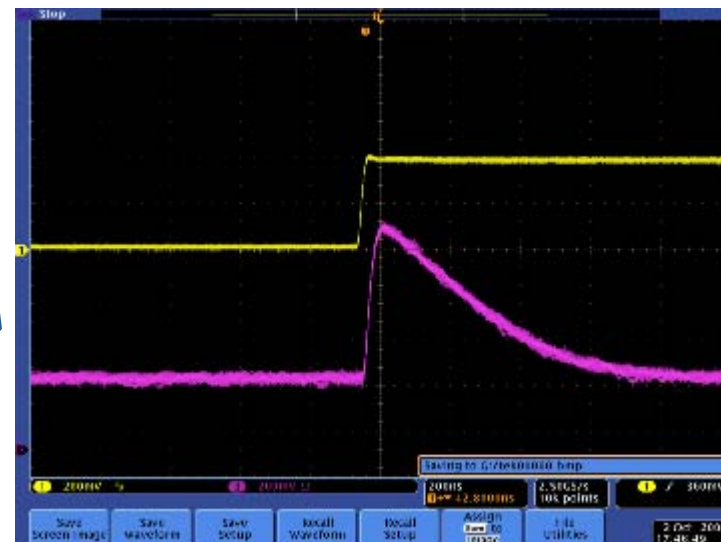
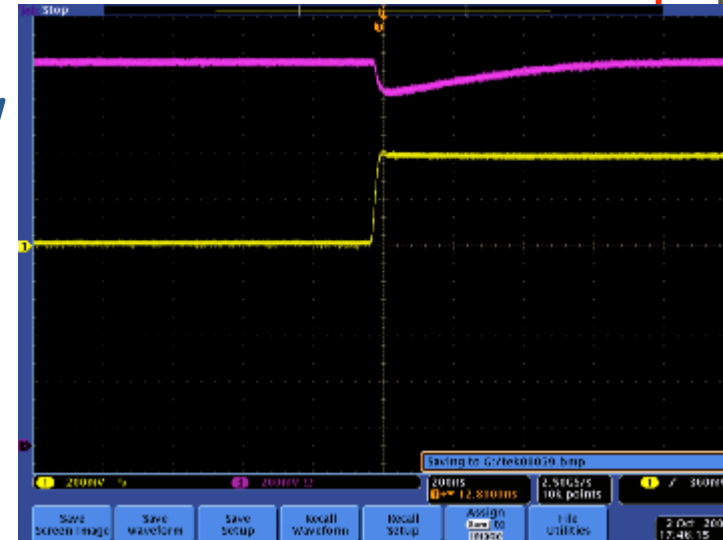
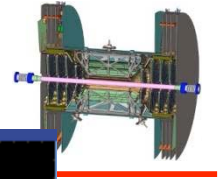
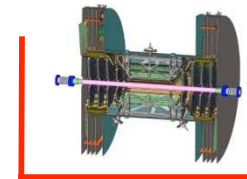


Figure 16.

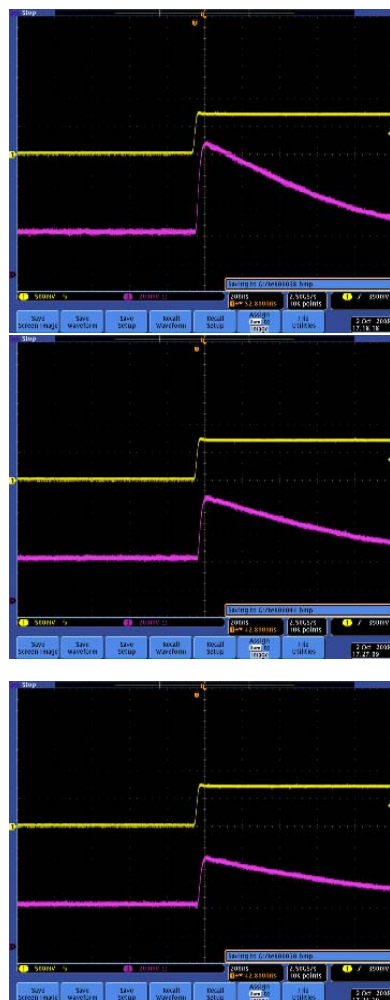
Test Bench Data



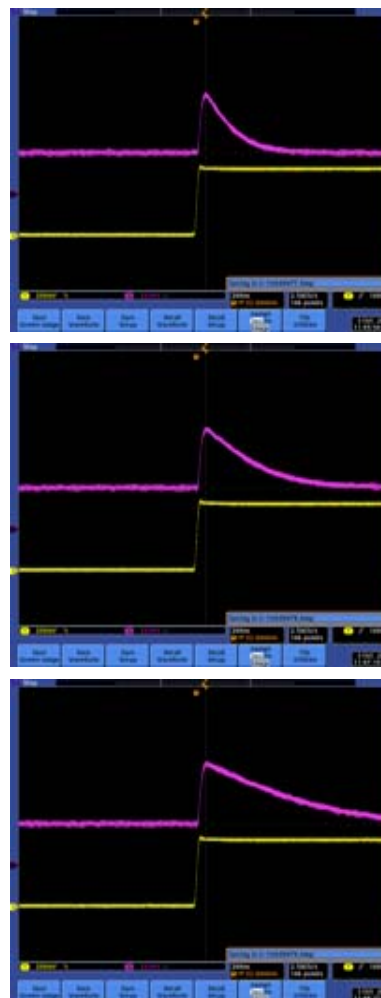
FPHX Programmable Bits



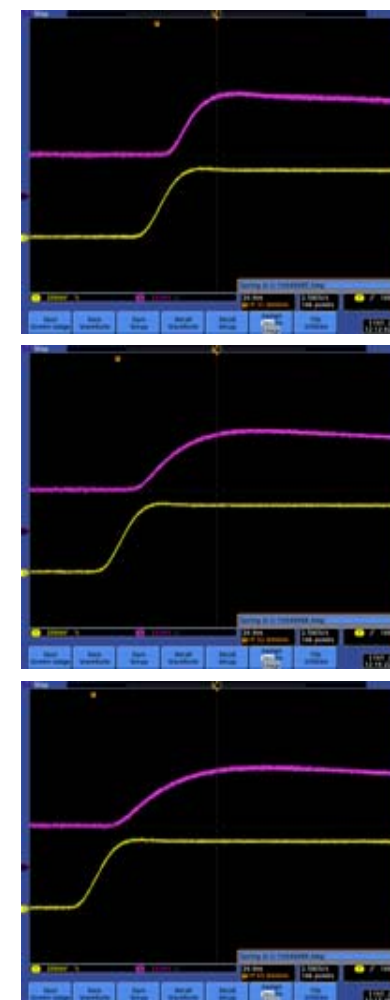
Gain



Fall time

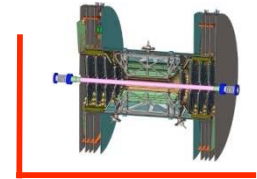


Rise time

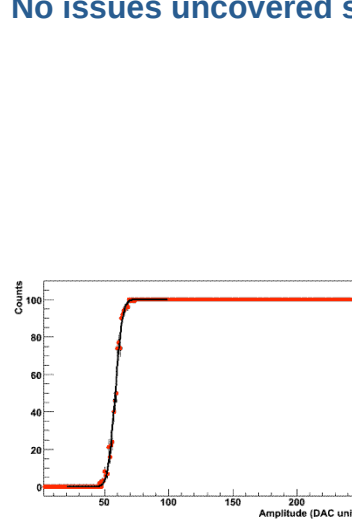
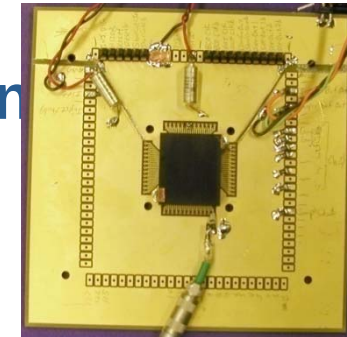




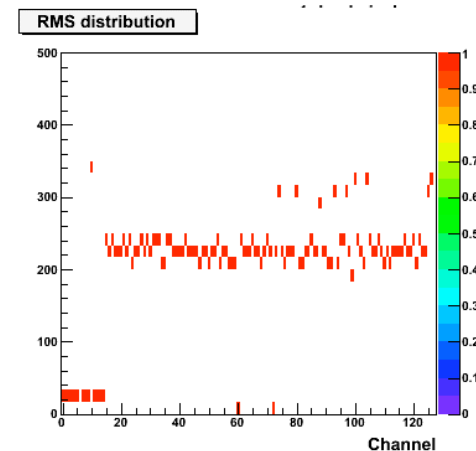
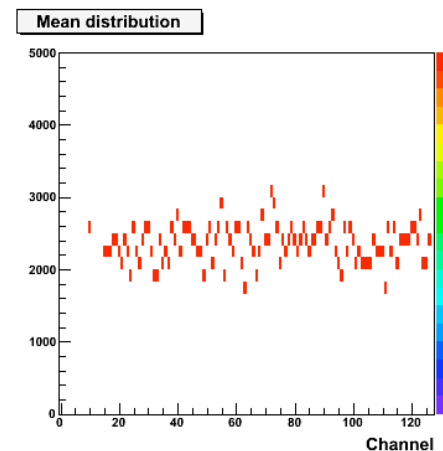
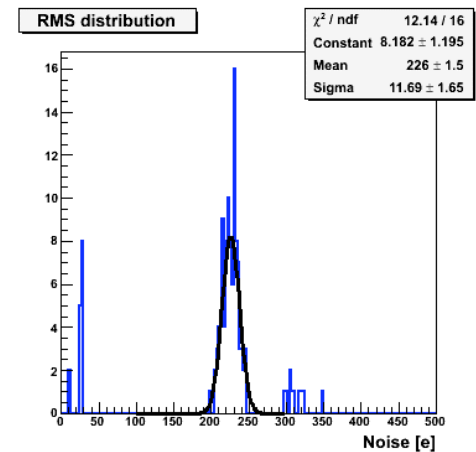
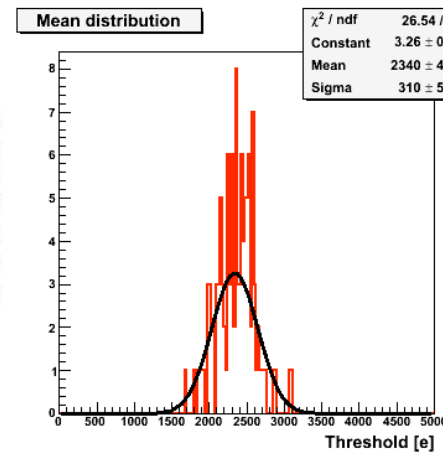
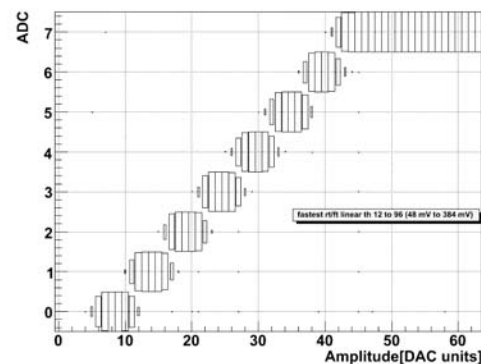
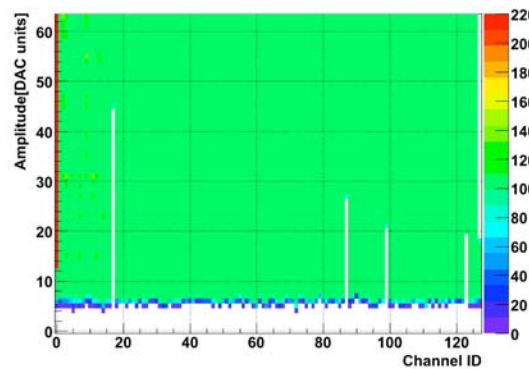
FVTX Technical Status - FPHX Testing

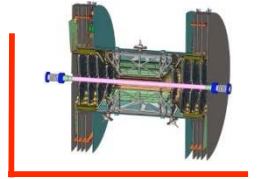


- ~200 electrons noise on most channels
- Threshold turn-on and distribution width as expected
- Programmable comparator thresholds work
- Known issues with 1st 15 channels because comparators are bonded out
- Overall performance is consistent with design specifications
- No issues uncovered so far



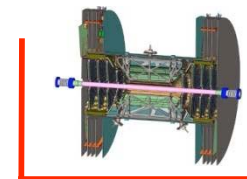
threshold turn-on curve





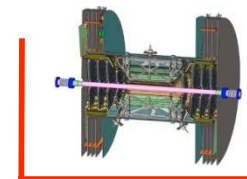
QA FPHX readout chip

- Prototype bench tests at LANL and FNAL (Zimmerman and Hoff-FNAL, Kapustinsky, Brooks, McGaughey, Butsyk-LANL, Banerjee-UNM and Winter-Columbia)
- Bench tests analog and digital performance, setup parameter sensitivity, stability and system robustness
- System test with FPHX + HDI + Readout
- Probe station to test reference voltages and currents, noise and gain



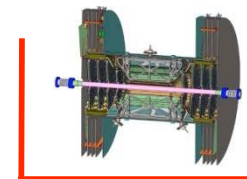
QA FPHX manpower and facilities

- Bench test stand facilities at FNAL, LANL, and soon UNM, and Columbia
- FNAL wafer probe station will be available for prototype and production testing
- Production will test 10-15 wafers, depending on yield (66% minimum assumption)
- Three months allotted for production wafer level tests, FNAL + students



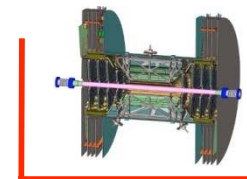
Sensor design, production and testing

WBS	Item	Date
1.4.1.2.1	Design prototype sensor mask	07/08/08 done
1.4.1.2.2	Process prototype sensors	10/28/08 done
1.4.1.2.3	Test prototypes	02/10/09 finish
1.4.1.2.4	Wire-bond sensor to FPHX	12/17/08 start
1.4.1.3.1	Submit production sensors	02/11/09 start
1.4.1.3.2	QA production sensors	09/15/09 finish



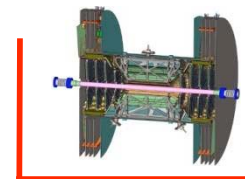
FPHX design, production and testing

WBS	item	Date
1.4.2.3	FPHX layout design	04/10/08 done
1.4.2.6	Design review	04/14/08 done
1.4.2.4.1	Submission to MOSIS	08/22/08 done
1.4.2.4.2	Prototype tests	10/10/08 ongoing
1.4.2.4.3, 1.4.2.4.4	Submit second prototype run	03/25/09 start
1.4.2.4.5	Test second prototype	06/17/09 start
1.4.2.4.9	Second run performance	12/16/09
1.4.2.5.1	Submit engineering run (production run)	12/17/09 start
1.4.2.5.2	Test production wafers	04/01/10 start



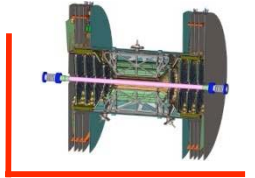
Summary

- Sensor design, mask and prototype production complete
- Sensor QA ongoing for the next several months, incl. FPHX
- Production sensor order scheduled February 09
- FPHX first round fully functional prototype complete
- Bench tests validate analog and digital performance specs
- FPHX second round submission scheduled March 09
- FPHX production submission scheduled December 09



Backup Slides

Hamamatsu Test Data



SerialNo. : 1 SerialNo. : 2 SerialNo. : 3 SerialNo. : 4 SerialNo. : 5
Vfd[V]: 60 Vfd[V]: 60 Vfd[V]: 60 Vfd[V]: 55 Vfd[V]: 60

VR/	Id[nA]	Ct[pA]	VR/	Id[nA]	Ct[pA]	VR/	Id[nA]	Ct[pA]	VR/	Id[nA]	Ct[pA]	VR/	Id[nA]	Ct[pA]
0	0.1	22013	0	0.0	21715	0	0.0	21811	0	0.0	21363	0	0.0	21679
5	30.0	3448	5	38.5	3134	5	25.1	3198	5	38.2	3001	5	33.5	3052
10	38.9	1853	10	50.2	1843	10	39.7	1825	10	49.5	1817	10	45.6	1814
15	42.3	1425	15	54.2	1417	15	43.1	1404	15	53.3	1399	15	49.1	1396
20	44.6	1202	20	56.8	1195	20	45.3	1183	20	55.7	1180	20	51.5	1177
25	46.5	1053	25	58.9	1046	25	47.1	1037	25	57.7	1033	25	53.5	1031
30	48.0	951	30	60.6	944	30	48.6	935	30	59.3	932	30	55.1	931
35	49.4	872	35	62.1	866	35	50.1	856	35	60.9	854	35	56.6	853
40	50.9	809	40	63.7	803	40	51.4	796	40	62.3	793	40	58.1	792
45	52.0	761	45	64.9	755	45	52.5	749	45	63.5	747	45	59.2	746
50	53.0	724	50	65.9	719	50	53.5	714	50	64.5	713	50	60.1	712
55	53.8	701	55	66.8	698	55	54.3	696	55	65.4	696	55	61.0	694
60	54.6	692	60	67.7	690	60	55.1	689	60	66.2	689	60	61.7	688
65	55.3	688	65	68.4	687	65	55.8	687	65	67.0	687	65	62.5	685
70	56.0	686	70	69.2	685	70	56.5	685	70	67.7	685	70	63.2	683
75	56.7	684	75	69.9	684	75	57.2	684	75	68.5	684	75	63.9	682
80	57.3	683	80	70.6	683	80	57.9	683	80	69.1	683	80	64.6	681
85	57.9	682	85	71.2	682	85	58.5	682	85	69.8	682	85	65.2	680
90	58.5	682	90	71.9	681	90	59.1	681	90	70.5	681	90	65.8	680
95	59.1	681	95	72.5	681	95	59.7	681	95	71.1	681	95	66.5	679
100	59.7	681	100	73.1	680	100	60.3	680	100	71.7	680	100	67.1	679
105	60.3	680	105	73.8	680	105	60.9	680	105	72.4	680	105	67.8	678
110	60.8	680	110	74.4	679	110	61.4	679	110	73.0	680	110	68.4	678
115	61.3	679	115	75.0	679	115	62.0	679	115	73.5	679	115	69.2	678
120	61.9	679	120	75.5	679	120	62.5	678	120	74.1	679	120	70.4	677
125	62.4	679	125	76.1	678	125	63.0	678	125	74.7	678	125	72.3	677
130	62.9	678	130	76.6	678	130	63.5	678	130	75.2	678	130	76.2	677
135	63.4	678	135	77.2	678	135	64.0	678	135	75.8	678	135	83.8	676
140	63.8	678	140	77.7	678	140	64.5	677	140	76.3	678	140	95.8	676
145	64.3	678	145	78.2	678	145	65.0	677	145	76.8	677	145	115.0	676
150	64.8	677	150	78.7	677	150	65.5	677	150	77.4	677	150	140.9	676
155	65.3	677	155	79.2	677	155	66.0	677	155	77.9	677	155	171.3	675
160	65.7	677	160	79.7	677	160	66.4	677	160	78.4	677	160	209.2	675
165	66.2	677	165	80.2	677	165	66.9	676	165	78.9	677	165	252.2	675
170	66.6	677	170	80.7	677	170	67.3	676	170	79.4	676	170	297.1	675
175	67.1	676	175	81.1	676	175	67.8	676	175	79.8	676	175	348.5	675
180	67.5	676	180	81.6	676	180	68.2	676	180	80.3	676	180	403.5	675
185	67.9	676	185	82.0	676	185	68.7	676	185	80.8	676	185	458.8	675
190	68.3	676	190	82.5	676	190	69.1	676	190	81.3	676	190	521.6	674
195	68.7	676	195	82.9	676	195	69.5	676	195	81.7	676	195	589.3	674
200	69.1	676	200	83.4	676	200	69.9	675	200	82.1	676	200	660.6	674

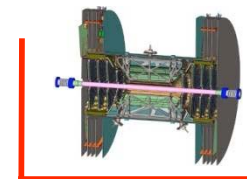
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nothing

NG channels:
nothing

NG channels:
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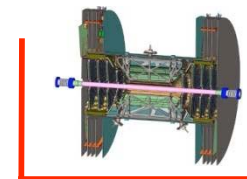
NG channels:
nothing

NG channels:
nothing



FVTX Sensor Costs (AY\$)

WBS	Item	Base	Actual cost	Quoted cost
1.4.1.2.1	Sensor mask set	\$51.8k	\$67.0k	
1.4.1.2.2	Sensor prototype	\$25.9k	\$36.9k	
1.4.1.2.3	Sensor production	\$439.2k		\$381.5k



FPHX Readout Chip Costs (AY\$)

WBS	Item	Base	Actual	Quoted
1.4.2.1.2	1 st FPHX proto run	\$0	\$175k	
1.4.2.4.4	2 nd FPHX proto run	\$194k		
1.4.2.5.1	Engineering FPHX run	\$260k		